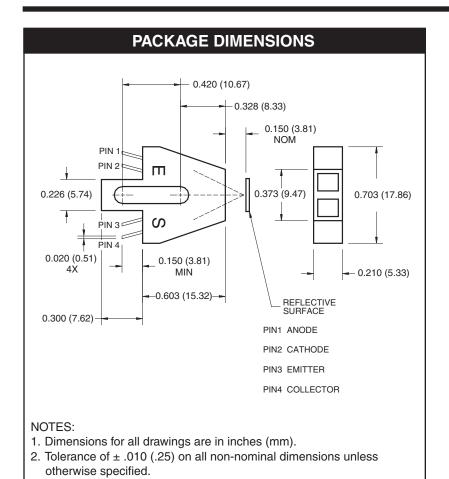
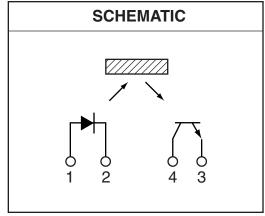


# PHOTOTRANSISTOR REFLECTIVE OBJECT SENSOR

## QRB1113 QRB1114







### **DESCRIPTION**

The QRB1113/1114 consists of an infrared emitting diode and an NPN silicon phototransistor mounted side by side on a converging optical axis in a black plastic housing. The phototransistor responds to radiation from the emitting diode only when a reflective object passes within its field of view. The area of the optimum response approximates a circle .200" in diameter.

### **FEATURES**

- · No contact surface sensing
- Phototransistor output
- · Focused for sensing specular reflection
- · Daylight filter on photosensor
- Dust cover



# **PHOTOTRANSISTOR** REFLECTIVE OBJECT SENSOR

# QRB1113 QRB1114

Parameter	Symbol	Rating	Units	
Operating Temperature	T <sub>OPR</sub>	-40 to +85	°C	
Storage Temperature	T <sub>STG</sub>	-40 to +85	°C	
Soldering Temperature (Iron)(2,3,4)	T <sub>SOL-I</sub>	240 for 5 sec	°C	
Soldering Temperature (Flow) <sup>(2,3)</sup>	T <sub>SOL-F</sub>	260 for 10 sec	°C	
EMITTER				
Continuous Forward Current	I <sub>F</sub>	50	mA	
Reverse Voltage	V <sub>R</sub>	5	V	
Power Dissipation <sup>(1)</sup>	P <sub>D</sub>	100	mW	
SENSOR				
Collector-Emitter Voltage	V <sub>CEO</sub>	30	V	
Emitter-Collector Voltage	V <sub>ECO</sub>	4.5	V	
Collector Current		20	mA	
Power Dissipation <sup>(1)</sup>	P <sub>D</sub>	100	mW	

#### **NOTES**

- 1. Derate power dissipation linearly 1.67 mW/°C above 25°C.
- RMA flux is recommended.
- Methanol or isopropyl alcohols are recommended as cleaning agents.
  Soldering iron 1/16" (1.6mm) minimum from housing.

- D is the distance from the assembly face to the reflective surface.
  Measured using an Eastman Kodak neutral test card with 90% diffused reflecting surface.
  Cross talk is the photo current measured with current to the input diode and no reflecting surface.

Parameter	Test Conditions	Cumbal	Min	Turn	Max	Units
	rest Conditions	Symbol	Min.	Тур.	Max.	Units
EMITTER						
Forward Voltage	I <sub>F</sub> = 40 mA	V <sub>F</sub>	_	_	1.7	V
Reverse Current	V <sub>R</sub> = 5.0 V	I <sub>R</sub>	_	_	100	μΑ
Peak Emission Wavelength	I <sub>F</sub> = 20 mA	λ <sub>PE</sub>	_	940	_	nm
SENSOR						
Collector-Emitter Breakdown Voltage	$I_C = 1 \text{ mA}$	BV <sub>CEO</sub>	30	_	_	V
Emitter-Collector Breakdown Voltage	I <sub>E</sub> = 0.1 mA	BV <sub>ECO</sub>	5	_	_	V
Collector-Emitter Dark Current	$V_{CE} = 10 \text{ V}, I_F = 0 \text{ mA}$	I <sub>CEO</sub>	_	_	100	nA
COUPLED						
On-state Collector Current	$I_{\rm F} = 40 \text{ mA}, V_{\rm CE} = 5 \text{ V}$					
QRB1113	$D = .150^{(5,6)}$	I <sub>C(ON)</sub>	0.20	_	_	mA
QRB1114	D = .150**(0,0)		0.60	_		
Collector-Emitter	$I_{\rm F} = 20 \text{ mA}, I_{\rm C} = 0.5 \text{ mA}$	V <sub>CE (SAT)</sub>	_	_	0.4	V
Saturation Voltage	IF = 20 IIIA, IC = 0.5 IIIA					
Rise Time	$V_{CE} = 5 \text{ V}, R_{L} = 100 \text{ V}$	t <sub>r</sub>	_	8	_	μs
Fall Time	$I_{C(ON)} = 5 \text{ mA}$	t <sub>f</sub> —	_	8	_	
Cross Talk	$I_F = 40 \text{ mA}, V_{CF} = 5 V^{(7)}$	I <sub>CX</sub>	_	_	1.00	μA

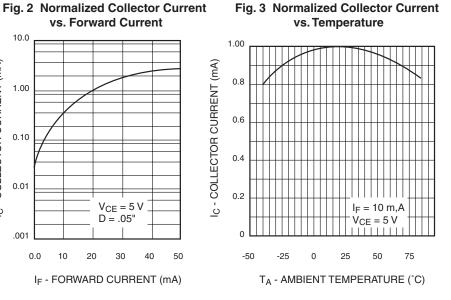
# **PHOTOTRANSISTOR** REFLECTIVE OBJECT SENSOR

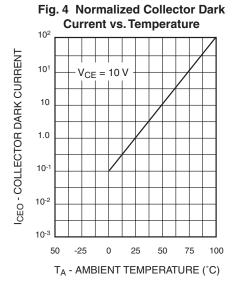
#### **QRB1113 QRB1114**

## **TYPICAL PERFORMANCE CURVES**

Fig. 1 Forward Voltage vs. Forward Current 1.60 1.40 VF - FORWARD VOLTAGE (V) 1.20 1.00 0.80 0.60 0.40 0.20 0.1 1.0 10 100 IF - FORWARD CURRENT (mA)

vs. Forward Current 10.0 I<sub>C</sub> - COLLECTOR CURRENT (mA) 1.00 0.10 0.01  $V_{CE} = 5 V$ D = .05" .001 0.0 10 20 30 40 50 IF - FORWARD CURRENT (mA)





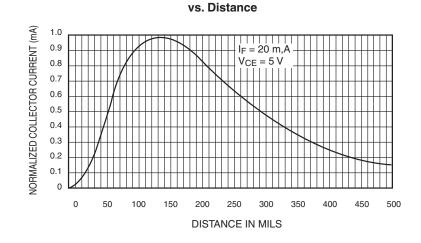


Fig. 5 Normalized Collector Current



# PHOTOTRANSISTOR REFLECTIVE OBJECT SENSOR

QRB1113 QRB1114

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